To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

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   Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SC2619

Silicon NPN Epitaxial

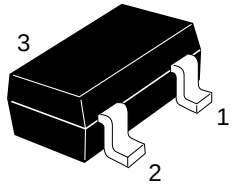
ADE-208-1070 (Z)
1st. Edition
Mar. 2001

Application

High frequency amplifier

Outline

MPAK



1. Emitter
2. Base
3. Collector

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	30	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Collector power dissipation	P_C	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

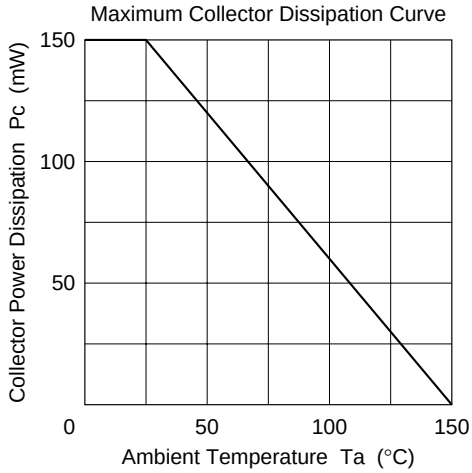
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	—	—	V	I_C = 10 µA, I_E = 0
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	30	—	—	V	I_C = 1 mA, R_{BE} =
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	I_E = 10 µA, I_C = 0
Collector cutoff current	I_{CBO}	—	—	0.5	µA	V_{CB} = 20 V, I_C = 0
Emitter cutoff current	I_{EBO}	—	—	0.5	µA	V_{EB} = 2 V, I_C = 0
DC current transfer ratio	h_{FE}*[1]	35	—	200		V_{CE} = 12 V, I_C = 2 mA
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.1	V	I_C = 10 mA, I_B = 1 mA
Base to emitter voltage	V_{BE}	—	—	0.75	V	V_{CE} = 12 V, I_C = 2 mA
Gain bandwidth product	f_T	—	230	—	MHz	V_{CE} = 12 V, I_C = 2 mA
Collector output capacitance	Cob	—	—	3.5	pF	V_{CB} = 10 V, I_E = 0, f = 1 MHz
Noise figure	NF	—	5.0	—	dB	V_{CE} = 6 V, I_C = 2 mA, f = 1 MHz, R_g = 500 Ω

Note: 1. The 2SC2619 is grouped by h_{FE} as follows.

Grade	A	B	C
Mark	FA	FB	FC
h_{FE}	35 to 75	60 to 120	100 to 200

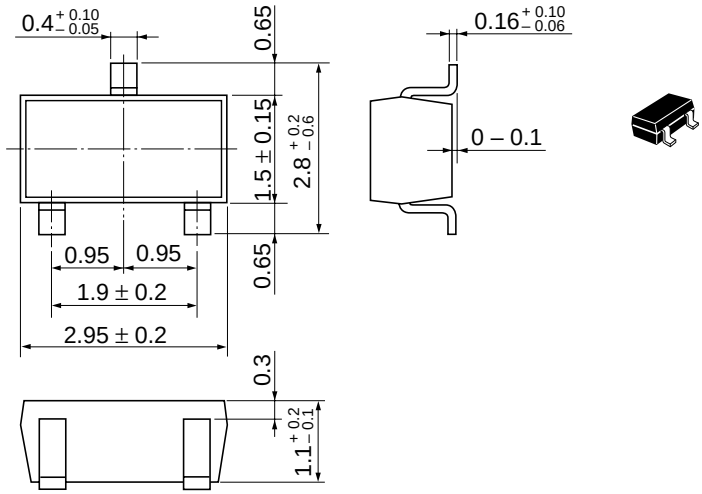
See characteristic curves of 2SC460.


Maximum Collector Dissipation Curve
Collector Power Dissipation Pc (mW)
150
100
50
0
50
100
150
Ambient Temperature Ta (°C)

Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	MPAK
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.011 g

Cautions

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